

# Design & Simulate 13

ECE2204 CRN:82929

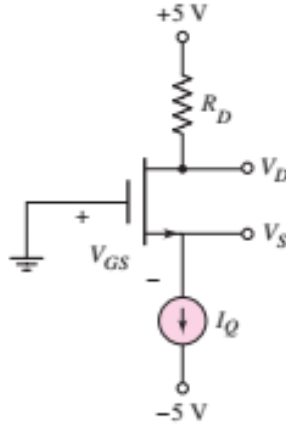
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## Problem 15.3-8.a.1:

### Design

Modify the circuit below to replace the current source with a resistor  $R_S$  and preserve the quiescent point. Design  $W/L$  and  $R_D$  to bias  $I_d = 250\mu A$  and  $V_S = -2.25V$ . Let  $k'_n$  vary by  $\pm 5\%$ . Compare the stabilities of the Q-points of the two bias schemes (current source vs. resistive) by comparing the % variations of  $I_{dQ}$ ,  $V_{dsQ}$ , and  $V_{gsQ}$ . Assume  $V_T = 0.8V$ ,  $k'_n = 80\mu A/V^2$ ,  $V_G = 0$



$$V_{GS} = V_G - V_S = 0V + 2.25V = 2.25V$$

$$I_D = \frac{k'_n}{2} \times \frac{W}{L} (V_{GS} - V_{TN})^2$$

$$\frac{W}{L} = \frac{2I_D}{k'_n (V_{GS} - V_{TN})^2} = \frac{2(250\mu A)}{(80\mu A/V^2)(2.25V - 0.8V)^2} = 2.97$$

$$V_{R_D} = \frac{V_{DD} - V_S}{2} = \frac{5 + 2.25V}{2} = 3.625V$$

$$R_D = \frac{V_{R_D}}{I_D} = \frac{3.625V}{250\mu A} = 14.5k\Omega$$

$$V_{R_S} = V_S - V_{SS} = -2.25V + 5V = 2.75V$$

$$R_S = \frac{V_{R_S}}{I_D} = \frac{2.75V}{250\mu A} = 11k\Omega$$

Evaluating Modes

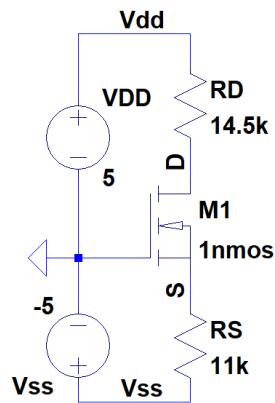
$$\begin{aligned}
k'_n &= [76, 80, 84]\mu A/V^2 \\
V_{DG} &= V_T = 0.8V \\
V_D &= V_G + V_{DG} = 0 + 0.8V = 0.8V \\
I_D &= \frac{5V - 0.8V}{14.5k\Omega} = 289.7\mu A \\
V_{RS} &= R_S I_D = (11k\Omega)(289.7\mu A) = 3.1867V \\
V_S &= V_{SS} + V_{RS} = -5V + 3.1867V = -1.813V \\
V_{GS} &= V_G - V_S = 0 + 1.813V = 1.813V \\
V'_{GS} &= \sqrt{\frac{2I_D}{K'_n} \frac{W}{L}} + |V_T| = \sqrt{\frac{2(289.7\mu A)}{[76, 80, 84]\mu A/V^2(2.97)}} + |0.8V| = [2.402, 2.362, 2.324]V
\end{aligned}$$

As all  $V'_{GS} > V_{GS}$ , the transistor is in saturation mode.

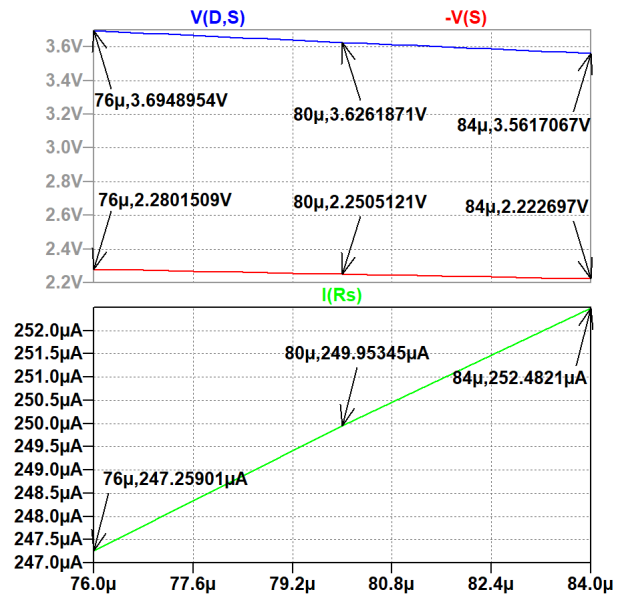
$$\begin{aligned}
V_{DS} &= V_{DD} - V_{SS} - I_D(R_D + R_S) = 5V + 5V - I_D(14.5k\Omega + 11k\Omega) = 10V - I_D(25.5k\Omega) \\
V_{GS} &= V_G - I_D R_S = -I_D(11k\Omega) \\
I_D &= \frac{K'_n W}{2L} (V_{GS} - V_T) \\
&= \frac{K'_n}{2} (2.97)(-I_D(11k\Omega) - 0.8V)(10V - I_D(25.5k\Omega))^2 \\
I_D(76\mu A/V^2) &= 402\mu A \\
I_D(80\mu A/V^2) &= 412\mu A \\
I_D(84\mu A/V^2) &= 420\mu A \\
V_{DS}(402\mu A) &= 10V - (402\mu A)(25.5k\Omega)
\end{aligned}$$

## Validation

LTSpice Implementation (values within  $< 1\%$ )



```
.model 1nmos NMOS
+(KP={Kp} W={W} L={L} Vto=0.8)
.param Vgs=2.25 Vds=5.875 Kp=80u W=2.97u L=1u
.step param KP list 76u 80u 84u
.op
```



I messed something up with this and have been fighting with it for days to no avail. I apologise for submitting this largely incomplete assignment so late.

This assignment should demonstrate a basic understanding of DC analysis of basic MOSFET circuits.

*I have neither given nor received unauthorized assistance on this assignment.*